# Abstracts

## High-Power MIC Diode Limiters for S- and X-Band Radars

*S. Hori, M. Kuroda, K. Kanema and S. Okano. "High-Power MIC Diode Limiters for S- and X-Band Radars." 1979 MTT-S International Microwave Symposium Digest 79.1 (1979 [MWSYM]): 329-331.*

S- and X-band passive MIC diode limiters have been developed for high power applications. Two PIN diodes with I layer thickness of 9.5mu m and 1.5mu m are shunt-mounted to 50 ohm microstrip lines. The limiters can handle 2-kW peak input power with less than 100mW peak leakage power for pulsed RF signals of 1mu s width and 0.1 percent duty ratio.

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